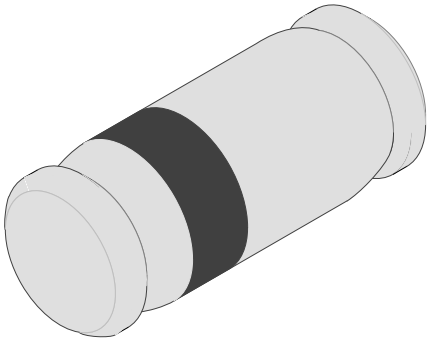
Mini Melf Switching diode

Features

- Electrical data identical with the devices 1N4148 and 1N4448 respectively
- Weight:0.03g



Applications

Extreme fast switches

Pb Free Product

Absolute Maximum Ratings

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	100	V
Reverse voltage			V_R	75	V
Peak forward surge current	t_p=1μs		I_{FSM}	2	A
Repetitive peak forward current			I_{FRM}	500	mA
Forward current			I_F	300	mA
Average forward current	V_R=0		I_{FAV}	150	mA
Power dissipation			P_V	500	mW
Operating junction temperature			T_j	-65~175	˚C
Storage temperature range			T_{stg}	-65~175	˚C

Maximum Thermal Resistance

T_j = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mmx50mmx1.6mm	R_{thJA}	500	K/W

Characteristics

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=5mA	MM4448	V_F	0.62		0.72	V
	I_F=50mA	MM4148	V_F		0.86	1	V
	I_F=100mA	MM4448	V_F		0.93	1	V
Reverse current	V_R=20V		I_R			25	nA
	V_R=20V, T_j=150˚C		I_R			50	μA
	V_R=75V		I_R			5	μA
Breakdown voltage	I_R=100μA, t_p/T=0.01, t_p=0.3ms		$V_{(BR)}$	100			V
Diode capacitance	V_R=0, f=1MHz, V_{HF}=50mV		C_D			4	pF
Rectification efficiency	V_{HF}=2V, f=100MHz		η_r	45			%
Reverse recovery time	I_F=I_R=10mA, i_R=1mA		t_{rr}			8	ns
	I_F=10mA, V_R=6V, i_R=0.1xI_R, R_L=100Ω		t_{rr}			4	ns

Typical Characteristics (T_j = 25°C unless otherwise specified)

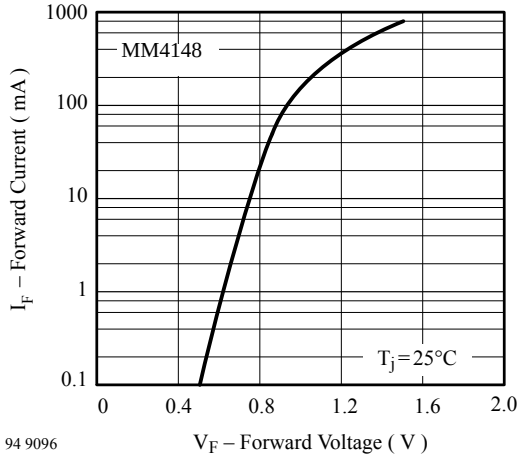


Figure 1. Forward Current vs. Forward Voltage

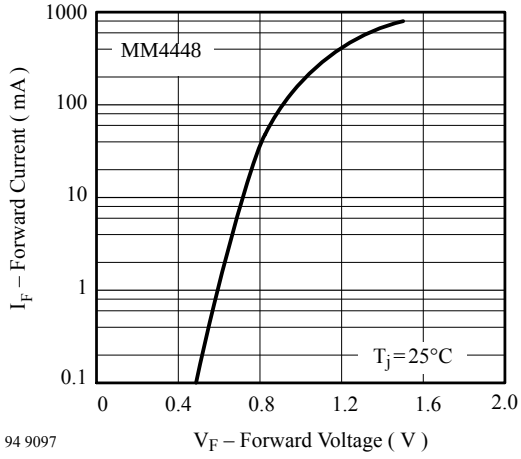


Figure 2. Forward Current vs. Forward Voltage

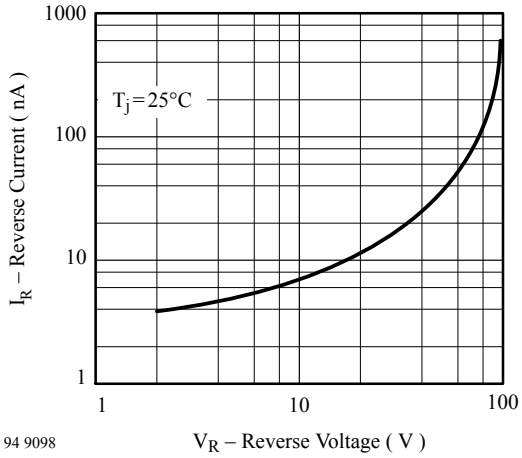


Figure 3. Reverse Current vs. Reverse Voltage

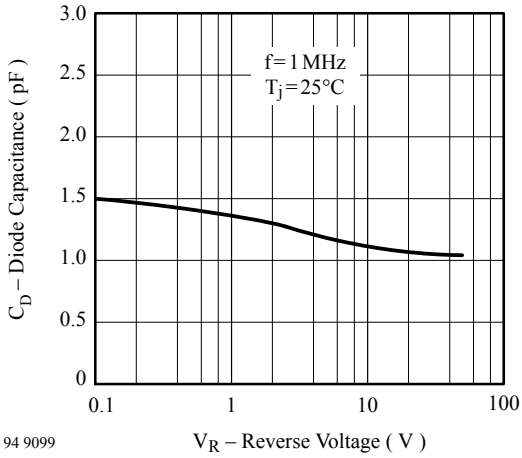


Figure 4. Diode Capacitance vs. Reverse Voltage

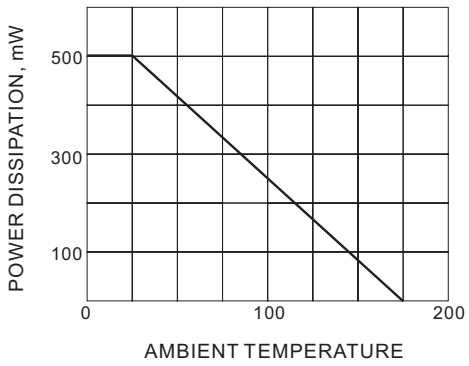


Figure 5. Derating Curve

Dimensions in mm